TM120P03D

P -Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

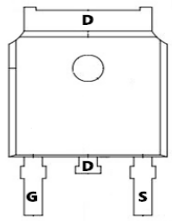
General Features

V_{DS} =-30V I_D =-120A

$R_{DS(ON)}$=3.0 mΩ (typ.)@V_{GS}=-10V

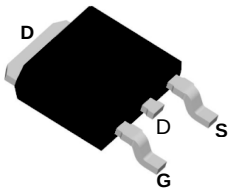
100% UIS Tested
100% R_g Tested

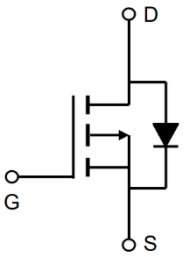
Green Product



Marking: 120P03

D:TO-252-3L





Absolute Maximum Ratings (TC=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ -10V[1,6]	-120	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ -10V[1,6]	-78	A
I_{DM}	Pulsed Drain Current[2]	-445	A
EAS	Single Pulse Avalanche Energy[3]	580	mJ
I_{AS}	Avalanche Current	-80	A
P_D@T_C=25℃	Total Power Dissipation[4]	100	W
T_{STG}	Storage Temperature Range	-55 to 175	℃
T_J	Operating Junction Temperature Range	-55 to 175	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1](t≦10S)	---	20	℃/W
	Thermal Resistance Junction-ambient [1](Steady State)	---	50	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-case [1]	---	3.6	℃/W

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ElectricalCharacteristics(T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=-250μA	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V, V_{GS}=0V			-1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	-1	-1.5	-2.0	V
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-20A		65		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=-10V, I_D=-20A		3.0	4.5	mΩ
		V_{GS}=-4.5V, I_D=-20A		4.4	5.5	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=-15V, V_{GS}=0V, f=1.0MHz		6500		pF
C_{oss}	Output Capacitance			820		pF
C_{rss}	Reverse Transfer Capacitance			540		pF
Rg	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1.0MHz		2.2		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=-10V, V_{DS}=-15V, R_L=0.75Ω, R_{GEN}=3Ω		14		nS
t_r	Turn-on Rise Time			13		nS
$t_{d(off)}$	Turn-Off Delay Time			65		nS
t_f	Turn-Off Fall Time			37		nS
Q_g	Total Gate Charge	V_{GS}=-10V, V_{DS}=-15V, I_D=-20A		130		nC
Q_{gs}	Gate-Source Charge			12		nC
Q_{gd}	Gate-Drain Charge			31		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				-120	A
V_{SD}	Forward on Voltage (Note 3)	V_{GS}=0V, I_S=-20A			-1.2	V
t_{rr}	Reverse Recovery Time	I_F=-20A, di/dt=100A/μs		30		ns
Q_{rr}	Reverse Recovery Charge	I_F=-20A, di/dt=100A/μs		40		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=15V,V_G=-10V, Rg=25Ω, L=0.5mH.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

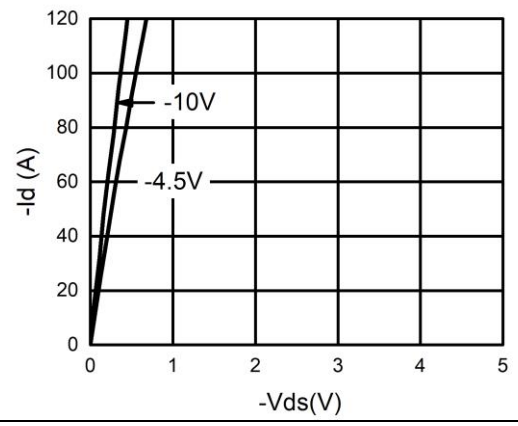


Figure 2. Transfer Characteristics

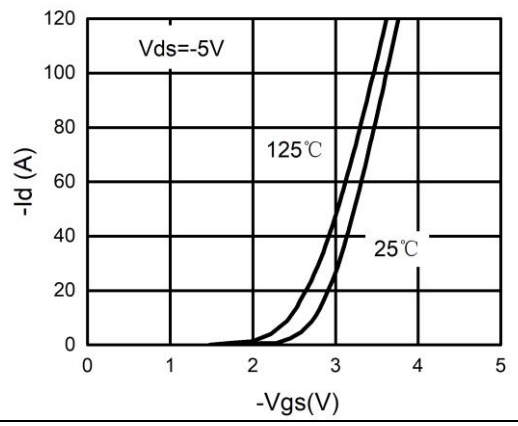


Figure 3. Power Dissipation

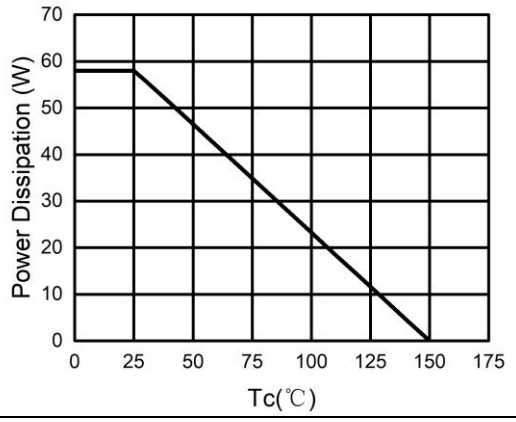


Figure 4. Drain Current

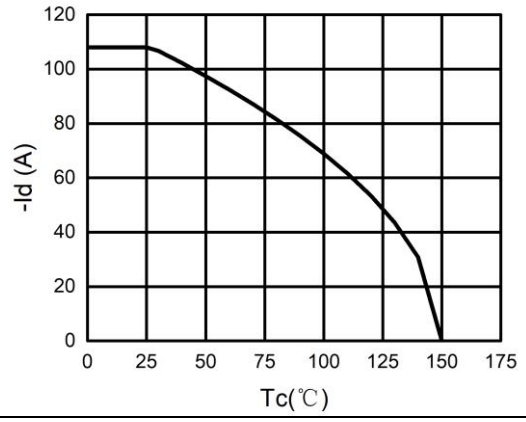


Figure 5. BV_{DSS} vs Junction Temperature

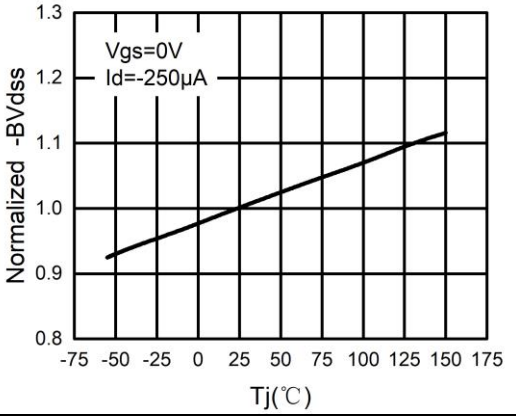


Figure 6. $R_{DS(ON)}$ vs Junction Temperature

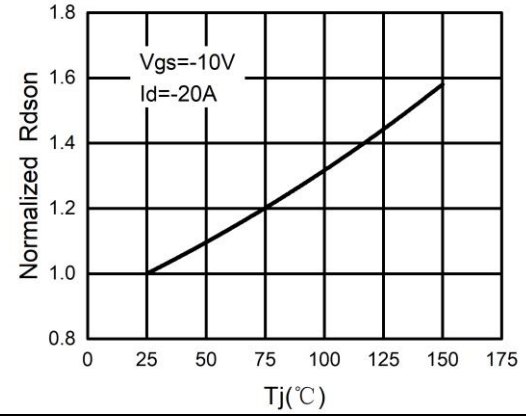


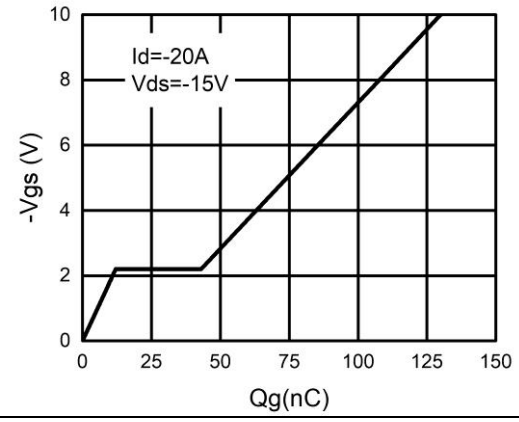
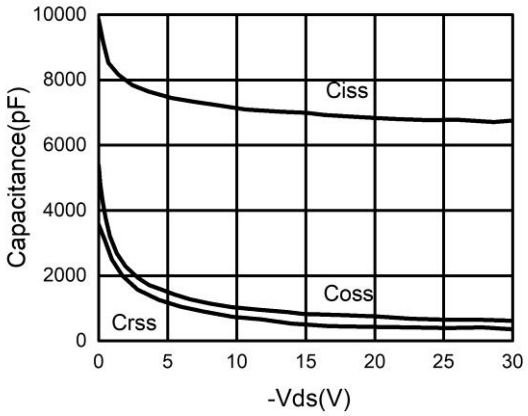
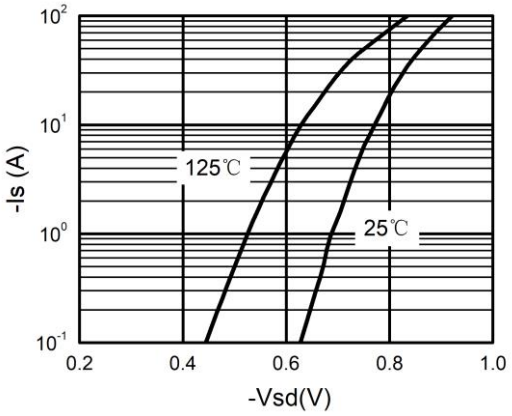
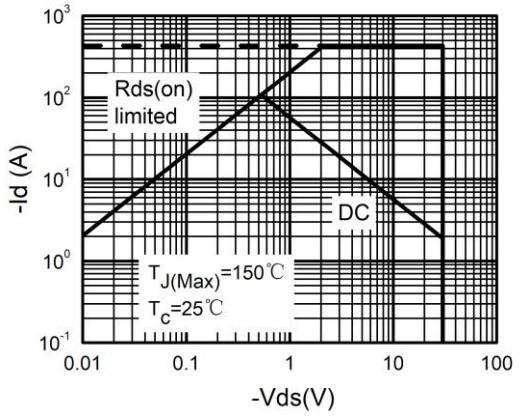
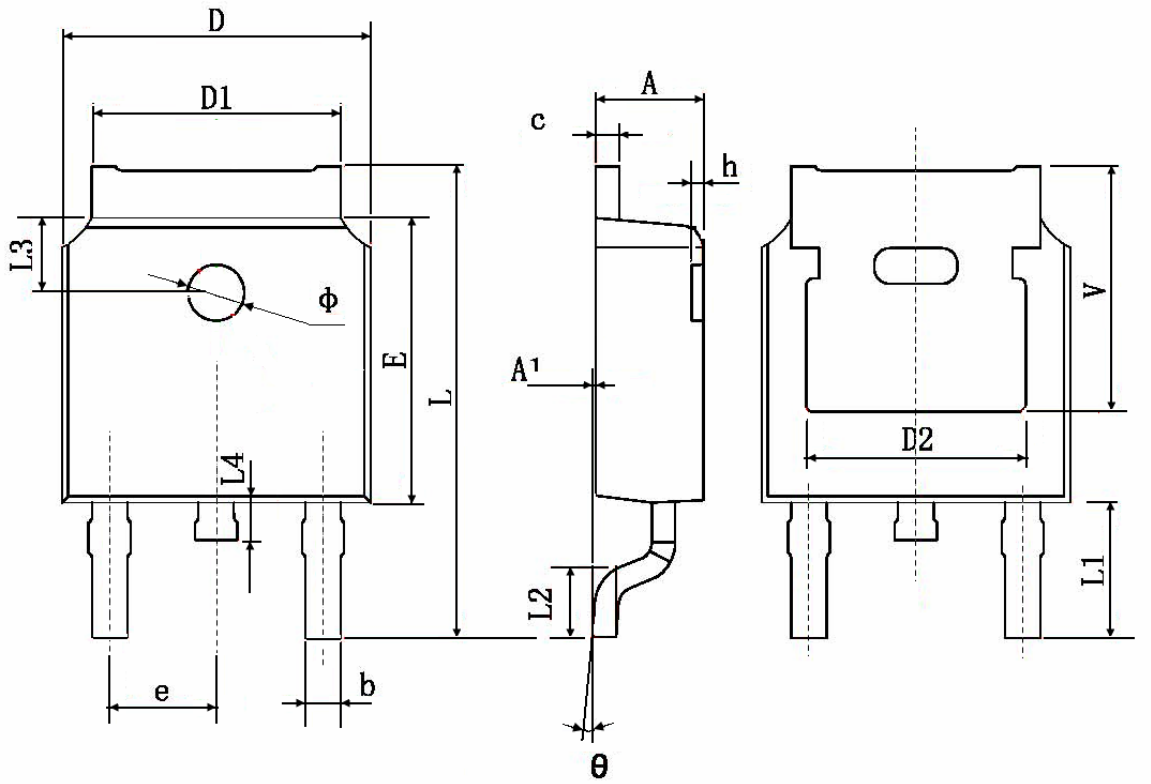
Figure 7. Gate Charge Waveforms	Figure 8. Capacitance
	

Figure 9. Body-Diode Characteristics	Figure 10. Maximum Safe Operating Area
	

Package Information:TO-252-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	